

Kuan Y Cheong

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

207
papers

3,620
citations

27
h-index

50
g-index

230
ext. papers

4,189
ext. citations

3
avg, IF

5.79
L-index

#	Paper	IF	Citations
207	Synergetic effects of monoethanolamine (MEA) and post-deposition calcination on biosynthesized CeO ₂ nanostructures spin-coated on silicon substrate. <i>Materials Chemistry and Physics</i> , 2022 , 278, 125656	4.4	0
206	A review of laser ablation and dicing of Si wafers. <i>Precision Engineering</i> , 2022 , 73, 377-408	2.9	2
205	Natural biomaterial honey-based resistive switching device for artificial synapse in neuromorphic systems. <i>Applied Physics Letters</i> , 2022 , 120, 083301	3.4	0
204	Buoyant titanium dioxide (TiO ₂) as high performance photocatalyst and peroxide activator: A critical review on fabrication, mechanism and application. <i>Journal of Environmental Chemical Engineering</i> , 2022 , 10, 107549	6.8	1
203	Performance of Organic Polymer Electrolyte Based on Extracted Aloe Vera Polysaccharide Compared with Mannose, Agarose and Carboxymethyl-Cellulose (CMC) for DSCs Application. <i>Springer Proceedings in Complexity</i> , 2021 , 431-439	0.3	
202	Study of synaptic properties of honey thin film for neuromorphic systems. <i>Materials Letters</i> , 2021 , 131169	3.3	1
201	Nonvolatile resistive switching memory based on monosaccharide fructose film. <i>Applied Physics Letters</i> , 2021 , 119, 163302	3.4	1
200	Titanium Dioxide/Polyvinyl Alcohol/Cork Nanocomposite: A Floating Photocatalyst for the Degradation of Methylene Blue under Irradiation of a Visible Light Source. <i>ACS Omega</i> , 2021 , 6, 14493-14503	3.9	7
199	Resistive Switching Properties of ZrO ₂ Film by Plasma-Enhanced Atomic Layer Deposition for Non-volatile Memory Applications. <i>Journal of Electronic Materials</i> , 2021 , 50, 5396	1.9	0
198	Resistive switching behaviour in a polymannose film for multistate non-volatile memory application. <i>Journal of Materials Chemistry C</i> , 2021 , 9, 1437-1450	7.1	5
197	Femtosecond laser dicing of ultrathin Si wafers with Cu backside layer - A fracture strength and microstructural study. <i>Journal of Manufacturing Processes</i> , 2021 , 62, 859-872	5	1
196	The adhesion of epoxy treated by microwave oxygen plasma. <i>Applied Surface Science</i> , 2021 , 563, 1502246	7	1
195	Review on resistive switching mechanisms of bio-organic thin film for non-volatile memory application. <i>Nanotechnology Reviews</i> , 2021 , 10, 680-709	6.3	11
194	High-k La ₂ Ce ₂ O ₇ for Passivation of Si Substrate. <i>Journal of Physics: Conference Series</i> , 2020 , 1535, 012030	3.3	
193	Mechanism study of SiO ₂ layer formation and separation at the Si die sidewall during nanosecond laser dicing of ultrathin Si wafers with Cu backside layer. <i>Applied Physics A: Materials Science and Processing</i> , 2020 , 126, 1	2.6	2
192	Investigation of honey thin film as a resistive switching material for nonvolatile memories. <i>Materials Letters</i> , 2020 , 271, 127796	3.3	7
191	Development and mechanical characterization of bilayer tubular scaffolds for vascular tissue engineering applications. <i>Journal of Materials Science</i> , 2020 , 55, 2516-2529	4.3	2

190	Investigation of honey as the electrolyte gate dielectrics of field effect transistors. <i>Microsystem Technologies</i> , 2020 , 26, 1717-1720	1.7	1
189	Artificial Synaptic Behavior of Aloe Polysaccharides-Based Device with Au as Top Electrode. <i>MRS Advances</i> , 2020 , 5, 693-698	0.7	1
188	Effects of Post-Deposition Annealing Time in Forming Gas Ambient on Y2O3 Films Deposited on Silicon Substrate. <i>Journal of Physics: Conference Series</i> , 2020 , 1535, 012031	0.3	
187	Effect of Template Deposition Method on Formation of AuNPs in Memory Devices Application. <i>Solid State Phenomena</i> , 2019 , 290, 67-74	0.4	
186	Switching Dynamics and Conductance Quantization of \$Aloe\$ Polysaccharides-Based Device. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 3110-3117	2.9	10
185	Fracture strength and microstructural study of ultrathin Si die with Cu backside layer diced with picosecond laser. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2019 , 759, 785-796	5.3	2
184	Post deposition annealing effect on properties of Y2O3/Al2O3 stacking gate dielectric on 4H-SiC. <i>Materials Letters</i> , 2019 , 245, 174-177	3.3	8
183	An improved three-point bending test method for the investigation of nanosecond laser dicing of ultrathin Si dies with Cu stabilization layer. <i>Materials Characterization</i> , 2018 , 136, 29-40	3.9	6
182	Effects of drying temperature on tomato-based thin film as self-powered UV photodetector. <i>Applied Surface Science</i> , 2018 , 445, 186-196	6.7	7
181	Effects of Oxalic Acid on UV-C Sensing Property of Tomato Thin-Film Based Photodetector. <i>Journal of Physics: Conference Series</i> , 2018 , 1082, 012054	0.3	
180	Scanning electron microscopy of soxhlet extracted aloe vera gel for electrolyte application. <i>Journal of Physics: Conference Series</i> , 2018 , 1123, 012070	0.3	1
179	Nonvolatile Memory Device Based on Bipolar and Unipolar Resistive Switching in Bio-Organic Aloe Polysaccharides Thin Film. <i>Advanced Materials Technologies</i> , 2018 , 3, 1800007	6.8	10
178	Stress and thermal characterization of 4H-SiC microelectromechanical structures. <i>Materials Letters</i> , 2017 , 191, 196-199	3.3	2
177	Filamentary Conduction in Aloe Vera Film for Memory Application. <i>Procedia Engineering</i> , 2017 , 184, 655-662		15
176	Aloe vera in active and passive regions of electronic devices towards a sustainable development 2017 ,		3
175	Effects of Various Heating Rate and Sintering Temperatures on the Microstructural and Die-Shear Strength of Sintered Ag-Cu Nanopaste. <i>Procedia Engineering</i> , 2017 , 184, 611-615		0
174	Memory properties of Au nanoparticles prepared by tuning HAuCl4 concentration using low-temperature hydrothermal reaction. <i>Thin Solid Films</i> , 2016 , 615, 84-90	2.2	3
173	Annealing temperature-dependent crystallinity and photocurrent response of anodic nanoporous iron oxide film. <i>Journal of Materials Research</i> , 2016 , 31, 1681-1690	2.5	5

172	Effects of rapid thermal annealing on structural, chemical, and electrical characteristics of atomic-layer deposited lanthanum doped zirconium dioxide thin film on 4H-SiC substrate. <i>Applied Surface Science</i> , 2016 , 365, 296-305	6.7	8
171	Effects of Electrode Materials on Charge Conduction Mechanisms of Memory Device Based on Natural Aloe Vera. <i>MRS Advances</i> , 2016 , 1, 2513-2518	0.7	11
170	Embedded Nanoparticles in Schottky and Ohmic Contacts: A Review. <i>Critical Reviews in Solid State and Materials Sciences</i> , 2015 , 40, 197-222	10.1	27
169	Au nanoparticles embedded at the interface of Al/4H-SiC Schottky contacts for current density enhancement. <i>Applied Physics A: Materials Science and Processing</i> , 2015 , 118, 315-325	2.6	11
168	Effects of annealing time on the electrical properties of the Y2O3 gate on silicon. <i>Journal of Experimental Nanoscience</i> , 2015 , 10, 19-28	1.9	17
167	Ultrathin Wafer Pre-Assembly and Assembly Process Technologies: A Review. <i>Critical Reviews in Solid State and Materials Sciences</i> , 2015 , 40, 251-290	10.1	25
166	Effects of drying temperature and ethanol concentration on bipolar switching characteristics of natural Aloe vera-based memory devices. <i>Physical Chemistry Chemical Physics</i> , 2015 , 17, 26833-53	3.6	78
165	Growth of gold nanoparticles using aluminum template via low-temperature hydrothermal method for memory applications. <i>Journal of Materials Science: Materials in Electronics</i> , 2015 , 26, 6484-6494	2.1	4
164	Green synthesis of iron oxide thin-films grown from recycled iron foils. <i>Materials Science in Semiconductor Processing</i> , 2015 , 29, 294-299	4.3	6
163	Thermal characteristic of sintered Ag ₂ O nanopaste for high-temperature die-attach application. <i>International Journal of Thermal Sciences</i> , 2015 , 87, 169-177	4.1	23
162	Investigation of Aloe Vera as active layer for development of organic based memory devices. <i>Materials Technology</i> , 2015 , 30, A29-A35	2.1	15
161	Effect of Nanosecond Laser Dicing on the Mechanical Strength and Fracture Mechanism of Ultrathin Si Dies With Cu Stabilization Layer. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2015 , 5, 1885-1897	1.7	5
160	Schottky barrier height engineering of Al contacts on Si by embedded Au nanoparticles. <i>Microelectronic Engineering</i> , 2015 , 133, 110-119	2.5	5
159	Surface Modification of Semiconductor by Simultaneous Thermal Oxidation and Nitridation 2015 , 2997-3029		
158	Direct formation of AuNPs thin film using thermal evaporated zinc as sacrificial template in hydrothermal method. <i>Journal of Materials Science: Materials in Electronics</i> , 2014 , 25, 2227-2236	2.1	4
157	Physical and Electrical Characteristics of Silver-Copper Nanopaste as Alternative Die-Attach. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2014 , 4, 8-15	1.7	18
156	Mechanical properties of sintered Ag ₂ O die-attach nanopaste for application on SiC device. <i>Materials & Design</i> , 2014 , 64, 166-176		22
155	Characterization of ultrathin Al ₂ O ₃ gate oxide deposited by RF-magnetron sputtering on gallium nitride epilayer on sapphire substrate. <i>Materials Chemistry and Physics</i> , 2014 , 148, 592-604	4.4	9

154	Investigation of SiO ₂ film growth on 4H-SiC by direct thermal oxidation and postoxidation annealing techniques in HNO ₃ & H ₂ O vapor at varied process durations. <i>Thin Solid Films</i> , 2014 , 570, 138-149	2.2	3
153	Physical and dispersive optical characteristics of ZrON/Si thin-film system. <i>Applied Physics A: Materials Science and Processing</i> , 2014 , 115, 1069-1072	2.6	18
152	Oxygen vacancy formation and annihilation in lanthanum cerium oxide as a metal reactive oxide on 4H-silicon carbide. <i>Physical Chemistry Chemical Physics</i> , 2014 , 16, 7015-22	3.6	25
151	Retardation mechanism of ultrathin Al ₂ O ₃ interlayer on Y ₂ O ₃ passivated gallium nitride surface. <i>ACS Applied Materials & Interfaces</i> , 2014 , 6, 7797-805	9.5	14
150	Effects of post-deposition annealing time in oxygen ambient on Y ₂ O ₃ film deposited on silicon substrate. <i>Materials Research Innovations</i> , 2014 , 18, S6-495-S6-498	1.9	12
149	Characterization Methods for Ultrathin Wafer and Die Quality: A Review. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2014 , 4, 2042-2057	1.7	19
148	Effects of Post-Deposition Annealing Time on Metal-Organic Decomposed Lanthanum Cerium Oxide Film Spin-Coated on Si Substrate. <i>Advanced Materials Research</i> , 2014 , 1024, 364-367	0.5	1
147	Effect of sintering environment on silver-copper die-attach nanopaste 2014 ,		1
146	Post-Deposition Annealing in Nitrous Oxide Ambient of RF-Magnetron Sputtered Y ₂ O ₃ Film on Silicon Substrate. <i>Advanced Materials Research</i> , 2014 , 1024, 360-363	0.5	2
145	Influence of post-deposition annealing time on oxygen gas sensing behaviour of Al/La _{0.5} Ce _{0.5} O _{1.75} /Si metal-oxide-semiconductor capacitor. <i>Materials Research Innovations</i> , 2014 , 18, S6-490-S6-494	1.9	2
144	Deposition of Gold Nanoparticles on Linker-Free Silicon Substrate by Spin-Coating. <i>Advanced Materials Research</i> , 2014 , 1024, 124-127	0.5	2
143	The Effect of Hydrothermal Reaction Time on Formation of AuNPs by Sacrificial Templated Growth Hydrothermal Approach. <i>Advanced Materials Research</i> , 2014 , 1024, 71-74	0.5	
142	Advances in Smart Materials and Applications. <i>Advances in Materials Science and Engineering</i> , 2014 , 1-1	1.5	
141	The effect of size and shape of gold nanoparticles on thin film properties. <i>Journal of Experimental Nanoscience</i> , 2014 , 9, 64-77	1.9	8
140	Thermal and photo reversible gel-sol transition of azobenzene based liquid crystalline organogel. <i>Journal of Photochemistry and Photobiology A: Chemistry</i> , 2014 , 278, 19-24	4.7	9
139	Effects of Post-deposition Annealing Time in Nitrogen Ambient on Y ₂ O ₃ Films Deposited on Silicon 2014 , 649-655		
138	Surface Modification of Semiconductor by Simultaneous Thermal Oxidation and Nitridation 2014 , 1-28		
137	Gold nanoparticles deposited on linker-free silicon substrate and embedded in aluminum Schottky contact. <i>Journal of Colloid and Interface Science</i> , 2013 , 408, 220-8	9.3	16

136	Recent development of gallium oxide thin film on GaN. <i>Materials Science in Semiconductor Processing</i> , 2013 , 16, 1217-1231	4.3	25
135	A novel silver/aluminium high-temperature die attach nanopaste system: the effects of organic additives content on post-sintered attributes. <i>Journal of Materials Science: Materials in Electronics</i> , 2013 , 24, 2678-2688	2.1	7
134	Effect of Oxidation Time on Thermally Grown Oxide on GaN. <i>Journal of Materials Engineering and Performance</i> , 2013 , 22, 1341-1347	1.6	7
133	Effects of post-deposition annealing ambient on band alignment of RF magnetron-sputtered Y2O3 film on gallium nitride. <i>Nanoscale Research Letters</i> , 2013 , 8, 53	5	11
132	Investigation of thermally grown oxide on 4H-SiC by a combination of H2O and HNO3 vapor with varied HNO3 solution heating temperature. <i>Applied Surface Science</i> , 2013 , 285, 795-804	6.7	5
131	Microstructural and optical properties of ZrON/Si thin films. <i>Materials Letters</i> , 2013 , 105, 72-75	3.3	27
130	Effects of post-deposition annealing ambient on chemical, structural, and electrical properties of RF magnetron sputtered Y2O3 gate on gallium nitride. <i>Journal of Alloys and Compounds</i> , 2013 , 575, 382-392	5.7	22
129	Ultralow Voltage Operation of $\text{Al}_x\text{La}_{1-x}\text{Ce}_z\text{O}_z/\text{SiC}$ for Oxygen Sensing. <i>IEEE Electron Device Letters</i> , 2013 , 34, 1430-1432	4.4	2
128	Physical and electrical attributes of sintered Ag80Al20 high temperature die attach material with different organic additives content. <i>Journal of Materials Science: Materials in Electronics</i> , 2013 , 24, 720-733	2.1	10
127	Effects of post-deposition annealing temperature on metal-organic decomposed lanthanum cerium oxide film as metal reactive oxide layer on 4H-SiC. <i>Materials Chemistry and Physics</i> , 2013 , 140, 622-633	4.4	16
126	Effect of Zinc Nitrate Concentration on Formation of AuNPs by Sacrificial Templated Growth Hydrothermal Approach and its Properties in Organic Memory Device. <i>Advanced Materials Research</i> , 2013 , 858, 67-73	0.5	
125	Current conduction mechanisms of RF-Magnetron sputtered Y2O3 gate oxide on gallium nitride. <i>Current Applied Physics</i> , 2013 , 13, 1433-1439	2.6	13
124	Study of molar ratio on the characteristics of metal-organic decomposed $\text{La}_x\text{Ce}_{1-x}\text{O}_z$ film as a metal reactive oxide on Si substrate. <i>Journal of Alloys and Compounds</i> , 2013 , 581, 793-800	5.7	16
123	Comparison of oxidized/nitrided Zr thin films on Si and SiC substrates. <i>Ceramics International</i> , 2013 , 39, S475-S479	5.1	7
122	Advances of Ag, Cu, and Ag/Cu alloy nanoparticles synthesized via chemical reduction route. <i>Journal of Nanoparticle Research</i> , 2013 , 15, 1	2.3	115
121	Reliability of sintered Ag80Al20 die attach nanopaste for high temperature applications on SiC power devices. <i>Microelectronics Reliability</i> , 2013 , 53, 473-480	1.2	15
120	Aloe vera gel as natural organic dielectric in electronic application. <i>Journal of Materials Science: Materials in Electronics</i> , 2013 , 24, 2646-2652	2.1	23
119	Fabrication of well-crystallized mesoporous ZrO2 thin films via Pluronic P123 templated sol-gel route. <i>Ceramics International</i> , 2013 , 39, S437-S440	5.1	9

118	Design of hierarchically mesoporous tetragonal ZrO ₂ thin films with tunable thickness by spin-coating via sol-gel template route. <i>Microporous and Mesoporous Materials</i> , 2013 , 167, 198-206	5.3	9
117	Surface passivation of gallium nitride by ultrathin RF-magnetron sputtered Al ₂ O ₃ gate. <i>ACS Applied Materials & Interfaces</i> , 2013 , 5, 6860-3	9.5	16
116	Structural and Chemical Studies of Metal-Organic Decomposed La ₂ CeO ₄ Thin Film as a Catalytic Oxide on 4H-SiC as a Function of Postdeposition Annealing Time. <i>Journal of Physical Chemistry C</i> , 2013 , 117, 14014-14024	3.8	18
115	Effect of spent bleaching earth based bio organic fertilizer on growth, yield and quality of eggplants under field condition 2013 ,		2
114	Nanoindentation of Porous Die Attach Materials as a Means of Determining Mechanical Attributes. <i>Applied Mechanics and Materials</i> , 2013 , 393, 57-62	0.3	
113	Effect of Sintering Temperature on Silver-Copper Nanopaste as High Temperature Die Attach Material. <i>Advanced Materials Research</i> , 2013 , 795, 47-50	0.5	9
112	Effects of SiO ₂ Nanoparticles on Dielectric Characteristic of Aloe Vera Paste. <i>Advanced Materials Research</i> , 2013 , 858, 74-79	0.5	2
111	Effects of wet-oxidized 4H-SiC annealed in HNO ₃ /H ₂ O vapour. <i>Microelectronics International</i> , 2013 , 31, 42-53	0.8	2
110	Formation of Anodic Oxide Nanotubes in H ₂ O ₂ - Fluoride Ethylene Glycol Electrolyte as Template for Electrodeposition of Fe ₂ O ₃ . <i>Advanced Materials Research</i> , 2013 , 832, 333-337	0.5	2
109	N-Type Organic Field-Effect Transistor Based on Fullerene with Natural Aloe Vera/SiO ₂ Nanoparticles as Gate Dielectric. <i>ECS Journal of Solid State Science and Technology</i> , 2013 , 2, P440-P444	2	13
108	Electrical study of ZrO ₂ /Si system formed at different oxidation/nitridation temperatures for extended duration in N ₂ O ambient. <i>Journal of Materials Research</i> , 2013 , 28, 2985-2989	2.5	2
107	Current Conduction Mechanisms in RF-Magnetron Sputtered Y ₂ O ₃ Gate on GaN Under Different Post-Deposition Annealing Ambient. <i>Science of Advanced Materials</i> , 2013 , 5, 1816-1827	2.3	6
106	Effects of oxidation and nitridation temperatures on electrical properties of sputtered Zr thin film based on Si in N ₂ O ambient. <i>Electronic Materials Letters</i> , 2012 , 8, 47-51	2.9	7
105	Influence of post-deposition annealing in oxygen ambient on metal-organic decomposed CeO ₂ film spin coated on 4H-SiC. <i>Journal of Materials Science: Materials in Electronics</i> , 2012 , 23, 257-266	2.1	20
104	Effects of applied voltage on the properties of anodic zirconia thin film on (100) silicon. <i>Thin Solid Films</i> , 2012 , 522, 117-124	2.2	4
103	Sintering of Ag ₈₀ -Al ₂₀ nanoalloy for high temperature die attach applications on silicon carbide-based power devices: The effects of ramp rate and dwell time 2012 ,		1
102	Growth of SiC nanowires using oil palm empty fruit bunch fibres infiltrated with tetraethyl orthosilicate. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2012 , 44, 2041-2049	3	8
101	Formation of Zr-oxynitride thin films on 4H-SiC substrate. <i>Thin Solid Films</i> , 2012 , 520, 6822-6829	2.2	22

100	Elaboration and characterization of sol-gel derived ZrO ₂ thin films treated with hot water. <i>Applied Surface Science</i> , 2012 , 258, 5250-5258	6.7	47
99	Effects of post-deposition annealing ambient on Y ₂ O ₃ gate deposited on silicon by RF magnetron sputtering. <i>Journal of Alloys and Compounds</i> , 2012 , 529, 73-83	5.7	35
98	Direct formation of gold nanoparticles on substrates using a novel ZnO sacrificial templated-growth hydrothermal approach and their properties in organic memory device. <i>Nanoscale Research Letters</i> , 2012 , 7, 563	5	8
97	Study on Gallium Nitride-Based Metal-Oxide-Semiconductor Capacitors With RF Magnetron Sputtered Y_{2}O_{3} Gate. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 3009-3016	2.9	18
96	Properties of thermally oxidized and nitrided Zr-oxynitride thin film on 4H-SiC in diluted N ₂ O ambient. <i>Materials Chemistry and Physics</i> , 2012 , 136, 624-637	4.4	8
95	Effect of oxidation temperature on physical properties of thermally grown oxide on GaN in N ₂ O ambient. <i>Materials Chemistry and Physics</i> , 2012 , 137, 381-388	4.4	5
94	Synthesis of SiC nanostructures through chemical vapor growth route. <i>Materialwissenschaft Und Werkstofftechnik</i> , 2012 , 43, 412-415	0.9	1
93	Growth of SiC nanowires and nanocones using mixture of oil palm fibres and rice husk ash. <i>Journal of Materials Science</i> , 2012 , 47, 5477-5487	4.3	17
92	Metal-oxide-semiconductor characteristics of lanthanum cerium oxide film on Si. <i>Applied Physics A: Materials Science and Processing</i> , 2012 , 107, 459-467	2.6	18
91	Sintering of Silver-Aluminum Nanopaste With Varying Aluminum Weight Percent for Use as a High-Temperature Die-Attach Material. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2012 , 2, 1940-1948	1.7	21
90	Metal-Oxide-Semiconductor Characteristics of Zr-Oxynitride Thin Film on 4H-SiC Substrate. <i>Journal of the Electrochemical Society</i> , 2012 , 159, H293-H299	3.9	18
89	Effects of Post-Deposition Annealing Temperature on Band Alignment and Electrical Characteristics of Lanthanum Cerium Oxide on 4H-SiC. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1433, 7		5
88	Effect of Sintering Time on Silver-Aluminium Nanopaste for High Temperature Die Attach Applications. <i>Advanced Materials Research</i> , 2012 , 576, 199-202	0.5	2
87	Effect of sputtering time on physical and electrical properties of ZrO _x thin film on Si. <i>Microelectronics International</i> , 2011 , 28, 7-11	0.8	
86	Die Attach Materials for High Temperature Applications: A Review. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2011 , 1, 457-478	1.7	254
85	Thermal oxidation and nitridation of sputtered Zr thin film on Si via N ₂ O gas. <i>Journal of Alloys and Compounds</i> , 2011 , 509, 8728-8737	5.7	33
84	Design and synthesis of mesoporous ZrO ₂ thin films using surfactant Pluronic P123 via sol-gel technique. <i>Journal of the Ceramic Society of Japan</i> , 2011 , 119, 517-521	1	6
83	Deposition and post-deposition annealing of thin Y ₂ O ₃ film on n-type Si in argon ambient. <i>Materials Chemistry and Physics</i> , 2011 , 130, 1007-1015	4.4	24

82	Effect of Postdeposition Annealing in Oxygen Ambient on Gallium-Nitride-Based MOS Capacitors With Cerium Oxide Gate. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 122-131	2.9	27
81	Band alignment and enhanced breakdown field of simultaneously oxidized and nitrided Zr film on Si. <i>Nanoscale Research Letters</i> , 2011 , 6, 489	5	18
80	Effect of process parameters on size, shape, and distribution of Sb ₂ O ₃ nanoparticles. <i>Journal of Materials Science</i> , 2011 , 46, 5129-5139	4.3	6
79	Oxidation of sputtered Zr thin film on Si substrate. <i>Journal of Materials Science: Materials in Electronics</i> , 2011 , 22, 143-150	2.1	25
78	Investigation of forming-gas annealed CeO ₂ thin film on GaN. <i>Journal of Materials Science: Materials in Electronics</i> , 2011 , 22, 583-591	2.1	24
77	Effects of post-deposition annealing temperature and ambient on RF magnetron sputtered Sm ₂ O ₃ gate on n-type silicon substrate. <i>Journal of Materials Science: Materials in Electronics</i> , 2011 , 22, 1816-1826	2.1	15
76	Controlled synthesis of Sb ₂ O ₃ nanoparticles by chemical reducing method in ethylene glycol. <i>Journal of Nanoparticle Research</i> , 2011 , 13, 2807-2818	2.3	12
75	Physical and electrical characteristics of metal-organic decomposed CeO ₂ gate spin-coated on 4H-SiC. <i>Applied Physics A: Materials Science and Processing</i> , 2011 , 103, 1067-1075	2.6	23
74	Effect of postdeposition annealing on electrical properties of RF-magnetron sputtered CeO _x gate on 4H-silicon carbide. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011 , 208, 1925-1930	1.6	2
73	Chemical reduction methods for synthesizing Ag and Al nanoparticles and their respective nanoalloys. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2011 , 176, 187-203	3.1	47
72	Effects of post-oxidation annealing temperature on ZrO ₂ thin film deposited on 4H-SiC substrate. <i>Materials Science in Semiconductor Processing</i> , 2011 , 14, 13-17	4.3	22
71	Effect of post-deposition annealing temperature on CeO ₂ thin film deposited on silicon substrate via RF magnetron sputtering technique. <i>Materials Science in Semiconductor Processing</i> , 2011 , 14, 101-107	4.3	12
70	A review on the synthesis of SiC from plant-based biomasses. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2011 , 176, 951-964	3.1	65
69	Comparison of metal-organic decomposed (MOD) cerium oxide (CeO ₂) gate deposited on GaN and SiC substrates. <i>Journal of Crystal Growth</i> , 2011 , 326, 2-8	1.6	33
68	Effects of post-deposition annealing temperature and time on physical properties of metal-organic decomposed lanthanum cerium oxide thin film. <i>Thin Solid Films</i> , 2011 , 519, 5139-5145	2.2	20
67	Influence of post-deposition annealing on metal-organic decomposed lanthanum cerium oxide film 2011 ,		5
66	Electrical Characteristics of Oxidized/Nitrided Zr Thin Film on Si. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H1270	3.9	21
65	FORTHCOMING GALLIUM NITRIDE BASED POWER DEVICES IN PROMPTING THE DEVELOPMENT OF HIGH POWER APPLICATIONS. <i>Modern Physics Letters B</i> , 2011 , 25, 77-88	1.6	6

64	Effects of N ₂ O Postdeposition Annealing on Metal-Organic Decomposed CeO ₂ Gate Oxide Spin-Coated on GaN Substrate. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H423	3.9	21
63	Electrical Properties of Pulsed Laser Deposited Y ₂ O ₃ Gate Oxide on 4H-SiC. <i>Electrochemical and Solid-State Letters</i> , 2010 , 13, H396		25
62	Improved 4H-SiC MOS Interface Produced by Oxidized-SiN Gate Oxide. <i>Materials Science Forum</i> , 2010 , 645-648, 511-514	0.4	2
61	Ag/PEPC/NiPc/ZnO/Ag thin film capacitive and resistive humidity sensors. <i>Journal of Semiconductors</i> , 2010 , 31, 054002	2.3	15
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